Product data sheet

1. Product profile

1.1 General description

Planar passivated very sensitive gate four quadrant triac in a SOT223 (SC-73) surface-mountable plastic package intended for applications requiring enhanced immunity to noise and direct interfacing to logic level ICs and low power gate drivers.

1.2 Features and benefits

- Direct interfacing to logic level ICs
- Enhanced current surge capability
- Enhanced noise immunity
- High blocking voltage of 800V
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants
- Very sensitive gate in four quadrants

1.3 Applications

- General purpose low power motor control
- Home appliances

- Industrial process control
- Low power AC Fan controllers

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	-	12.5	Α
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 105 ^{\circ}\text{C}$; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	1	Α



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Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{\text{ or } 100 \text{ C}}$	0.2	-	3	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{\text{ or } 100 \text{ cm}}$	0.2	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{\text{ or } 100000000000000000000000000000000000$	0.2	-	3	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G+;}$ $T_i = 25 \text{ °C; see } \frac{\text{Figure 9}}{\text{ Figure 9}}$	0.2	-	5	mA

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		N. I
2	T2	main terminal 2	4	T2—T1
3	G	gate		`G sym051
4	T2	main terminal 2	1 2 3	
			SOT223 (SOT223)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
Z0103NN0	SOT223	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
Z0103NN0	103NN0

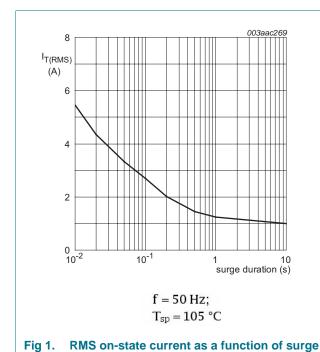
[1] % = placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 105$ °C; see Figure 3; see Figure 1; see Figure 2	-	1	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	12.5	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	13.8	Α
l ² t	I ² t for fusing	$t_p = 10 \text{ ms}$; sine-wave pulse	-	0.78	A^2s
dI _T /dt	rate of rise of on-state current	I_T = 1 A; I_G = 20 mA; dI_G/dt = 100 mA/ μ s; T2+ G+	-	50	A/µs
		I_T = 1 A; I_G = 20 mA; dI_G/dt = 100 mA/ μ s; T2+ G-	-	50	A/µs
		I_T = 1 A; I_G = 20 mA; dI_G/dt = 100 mA/ μ s; T2- G-	-	50	A/µs
		I_T = 1 A; I_G = 20 mA; dI_G/dt = 100 mA/ μ s; T2- G+	-	20	A/µs
I _{GM}	peak gate current		-	1	Α
P _{GM}	peak gate power		-	2	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C



duration; maximum values

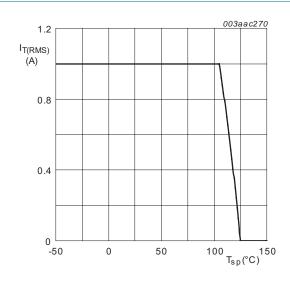


Fig 2. RMS on-state current as a function of solder point temperature; maximum values

Z0103NN0

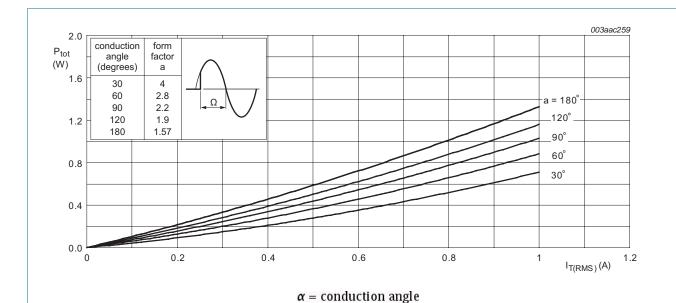


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

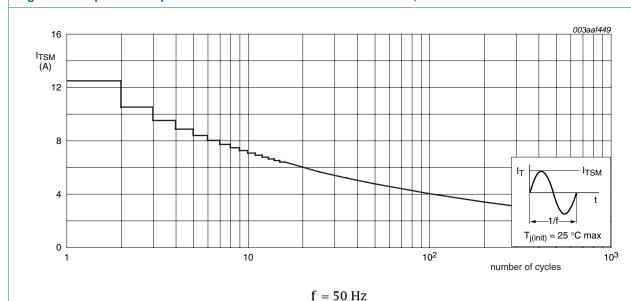
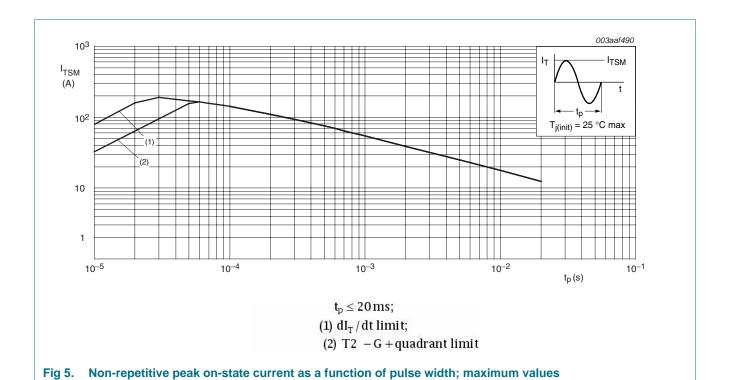


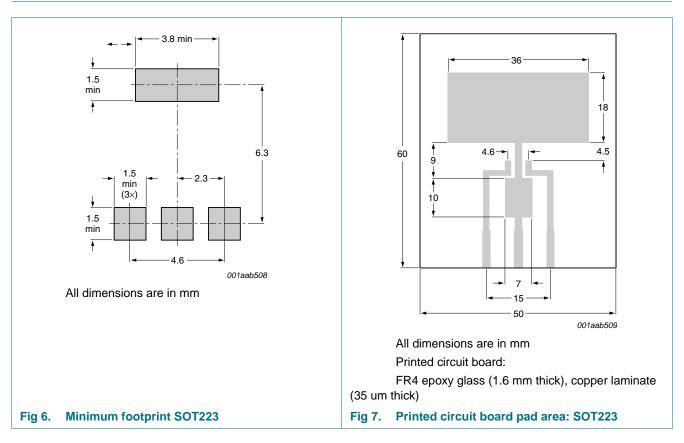
Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



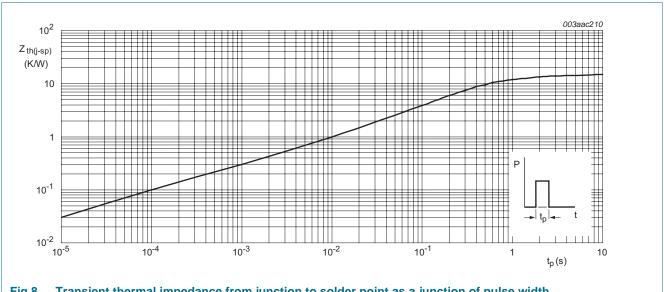
6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	full cycle; see <u>Figure 8</u>	-	-	15	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air; printed-circuit board mounted: minimum footprint; full cycle; see Figure 6	-	156	-	K/W
		in free air; printed-circuit board mounted: pad area; full cycle; see Figure 7	-	70	-	K/W



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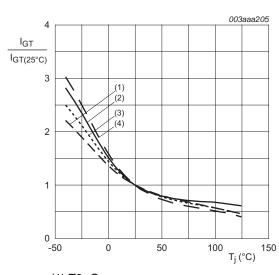


7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+; T_j = 25 \text{ °C;}$ see Figure 9	0.2	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-; T_j = 25 ^{\circ}C;$ see Figure 9	0.2	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G-; T_j = 25 °C;$ see Figure 9	0.2	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+; T_j = 25 ^C;$ see <u>Figure 9</u>	0.2	-	5	mA
L	latching current	$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2 + G+; T_j = 25 \text{ °C;}$ see Figure 10	-	-	7	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-; T_j = 25 ^{\circ}C;$ see <u>Figure 10</u>	-	-	20	mA mA mA mA mA V V W MA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G-; T_j = 25 °C;$ see <u>Figure 10</u>	-	-	7	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+}; T_j = 25 ^{\circ}\text{C};$ see Figure 10	-	-	7	mA
I _H	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 11}}{\text{ or } 100 \text{ J}}$	-	-	7	mΑ
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; see <u>Figure 12</u>	-	1.3	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 13</u>	-	-	1.3	V
		$V_D = 800 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C};$ see <u>Figure 13</u>	0.2	-	-	V
I _D	off-state current	$V_D = 800 \text{ V}; T_j = 125 ^{\circ}\text{C}$	-	-	0.5	mΑ
Dynamic ch	naracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 110 °C; gate open circuit; exponential waveform; see Figure 14	80	-	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 110 \text{ °C};$ $dI_{com}/dt = 0.44 \text{ A/ms}; \text{ gate open circuit}$	0.5	-	-	V/µs

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- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig 9. Normalized gate trigger current as a function of junction temperature

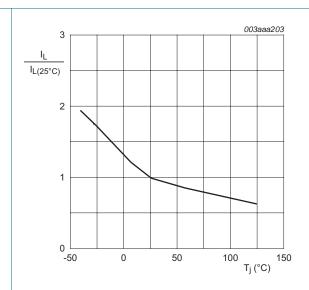


Fig 10. Normalized latching current as a function of junction temperature

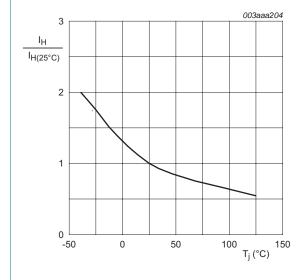
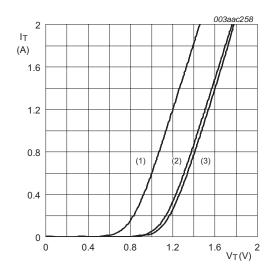


Fig 11. Normalized holding current as a function of junction temperature



 $V_0 = 1.13 \text{ V}$

 $R_s = 0.31 \Omega$

(1) T_i = 125 °C; typical values

(2) T_j = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig 12. On-state current as a function of on-state voltage

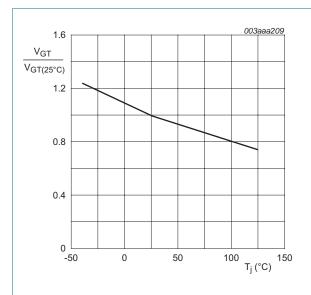


Fig 13. Normalized gate trigger voltage as a function of junction temperature

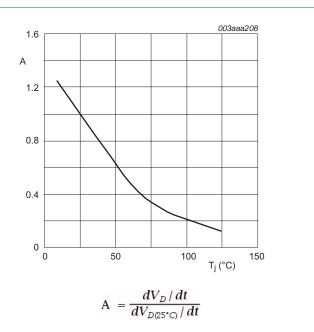


Fig 14. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

8. Package outline

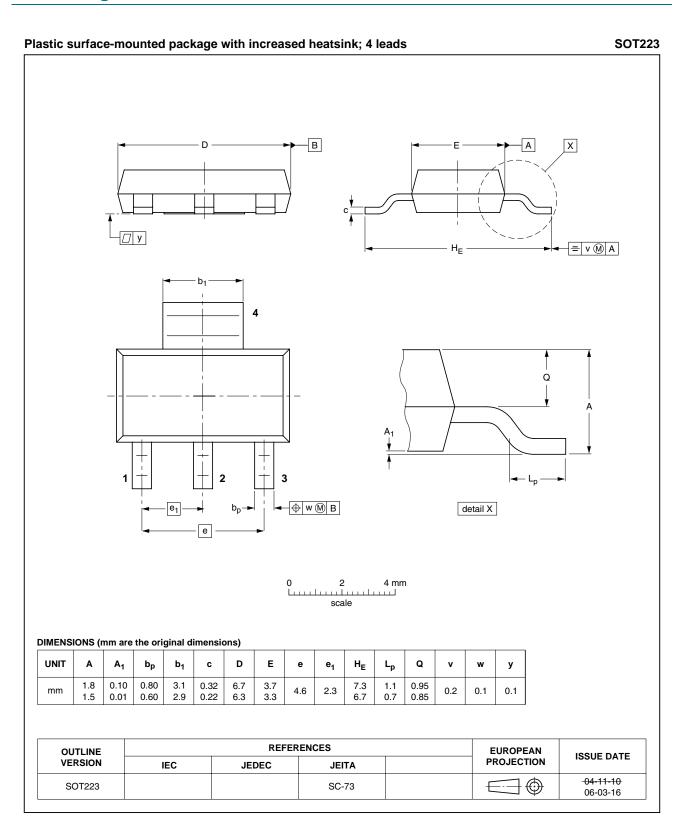


Fig 15. Package outline SOT223 (SOT223)

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9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
Z0103NN0 v.2	20110321	Product data sheet	-	Z0103NN0 v.1
Modifications:	 Various changes 	to content.		
Z0103NN0 v.1	20110103	Product data sheet	-	-

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10. Legal information

10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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